NSN 5961-01-466-7199

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Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-466-7199 **Inclosure Material:** Metal **Overall Length:** 0.800 inches **Terminal Length:** 0.600 inches **Overall Width:** 0.437 inches **End Application:** E/ifscmir sensor assembly **Mounting Facility Quantity: Mounting Method:** Threaded hole **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 500.0 reverse voltage, peak and 500.0 reverse voltage, instantaneous and 350.0 reverse voltage, total rms **Current Rating Per Characteristic:** 15.00 amperes forward current, total rms megahertz and 60.00 amperes source cutoff current outside diameter **Power Rating Per Characteristic:** 41.0 watts small-signal output power, common-base preset **Capacitance Rating In Picofarads:** 150.0 **Maximum Operating Tempurature Per Measurement Point:** -65.0 degrees celsius case and 175.0 degrees celsius case **Test Data Document:** 0af43-206656 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 1 unthreaded hole Shelf Life: N/a **Unit Of Measure: Demilitarization:**